

SCOPE: CMOS, BUFFERED, MULTIPLYING 8-BIT D/A CONVERTER

| <u>Device Type</u> | <u>Generic Number</u> | <u>Circuit Function</u> |
|--------------------|-----------------------|-------------------------|
| 01 | MX7528S(x)/883B | DAC with ± 4 LSB |
| 02 | MX7528T(x)/883B | DAC with ± 2 LSB |
| 03 | MX7528U(x)/883B | DAC with ± 1 LSB |

Case Outline(s). The case outlines shall be designated in Mil-Std-1835 and as follows:

| <u>Outline Letter</u> | <u>Mil-Std-1835</u> | <u>Case Outline</u> | <u>Package Code</u> |
|-----------------------|------------------------|---------------------|---------------------|
| Q | GDIP1-T20 or CDIP2-T20 | 20 LEAD CERDIP | J20 |

Absolute Maximum Ratings:

| | |
|--|-------------------------|
| V_{DD} to AGND | 0V, +17V |
| V_{DD} to DGND | 0V, +17V |
| V_{RFBA} , V_{RFBB} to DGND | ± 25 V |
| V_{REFA} , V_{REFB} to AGND | ± 25 V |
| Digital Input Voltage to DGND | -0.3V to $V_{DD}+0.3$ V |
| V pin 1 to DGND | -0.3V to V_{DD} |
| V pin 2, V pin 20 to AGND | -0.3V to $V_{DD}+0.3$ V |
| AGND to DGND | -0.3V, $V_{DD}+0.3$ V |
| DGND to AGND | +0.3V |
| Lead Temperature (soldering, 10 seconds) | +300°C |
| Storage Temperature | -65°C to +150°C |
| Continuous Power Dissipation | $T_A=+70^\circ\text{C}$ |
| 20 pin CERDIP(derate 11.1mW/°C above +70°C) | 889mW |
| Junction Temperature T_J | +150°C |
| Thermal Resistance, Junction to Case, θ_{JC} | |
| 20 pin CERDIP..... | 40°C/W |
| Thermal Resistance, Junction to Ambient, θ_{JA} : | |
| 16 pin CERDIP..... | 90°C/W |

Recommended Operating Conditions

| | |
|---|---|
| Ambient Operating Range (T_A) | -55°C to +125°C |
| Supply Voltage Range (V_{DD}) | +4.75V to +5.25V and +14.25V to +15.75V |
| V_{REF} DAC A= V_{REF} DAC B | +10V |
| OUT DAC A=OUT DAC B | 0V |

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TABLE 1. ELECTRICAL TESTS:

| TEST | Symbol | CONDITIONS | Group A Subgroup | Device type | Limits Min | Limits Max | Units |
|---|--------------------|---|------------------|----------------|-------------|----------------------|--------|
| | | -55 °C ≤ T _A ≤ +125 °C <u>1</u> / Unless otherwise specified | | | | | |
| ACCURACY | | | | | | | |
| Resolution NOTE 4 | RES | V _{DD} =+5V and V _{DD} =+15V | 1,2,3 | All | 8.0 | | Bits |
| Relative Accuracy | RA | V _{DD} =+5V and V _{DD} =+15V | 1,2,3 | 01 | | ±1.0 | LSB |
| Relative Accuracy | RA | V _{DD} =+5V and V _{DD} =+15V | 1,2,3 | 02,03 | | ±0.5 | LSB |
| Differential Nonlinearity | DNL | V _{DD} =+5V and V _{DD} =+15V Monotonic to 8-Bits | 1,2,3 | All | -1 | 1 | LSB |
| Gain Error NOTE 2 | AE | V _{DD} =+5V and V _{DD} =+15V DAC register loaded with 1111 1111 1111 | 1 | 01 02 03 | | ±4.0 ±2.0 ±1.0 | LSB |
| Gain Error NOTE 2 | AE | V _{DD} =+5V V _{DD} =+15V | 2,3 | 01 | | ±6.0 ±5.0 | LSB |
| Gain Error NOTE 2 | AE | V _{DD} =+5V V _{DD} =+15V | 2,3 | 02 | | ±4.0 ±3.0 | LSB |
| Gain Error NOTE 2 | AE | V _{DD} =+5V V _{DD} =+15V | 2,3 | 03 | | ±3.0 ±1.0 | LSB |
| Power Supply Rejection | PSRR | V _{DD} =+5V, ΔV _{DD} =±5% | 1 2,3 | All | | ±0.02 ±0.04 | %/% |
| Power Supply Rejection | PSRR | V _{DD} =+15V, ΔV _{DD} =±5% | 1 2,3 | All | | ±0.01 ±0.02 | %/% |
| Output Leakage Current OUTA, OUTB | I _{OL} | V _{DD} =+5V, DAC latches loaded with 0000 0000 | 1 2,3 | All | | ±50 ±400 | nA |
| Output Leakage Current OUTA, OUTB | I _{OL} | V _{DD} =+15V, DAC latches loaded with 0000 0000 | 1 2,3 | All | | ±50 ±200 | nA |
| Reference Input Resistance VREFA, VREFB | R _{IN} | V _{DD} =+5V and +15V | 4,5,6 | All | 8 | 15 | kΩ |
| Digital Input High Voltage | V _{IH} | V _{DD} =+5V V _{DD} =+15V | 1,2,3 | All | 2.4 13.5 | | V |
| Digital Input Low Voltage | V _{IL} | V _{DD} =+5V V _{DD} =+15V | 1,2,3 | All | | 0.8 1.5 | V |
| Digital Input Leakage Current | I _{IN} | V _{DD} =+5V V _{IN} =0V or V _{DD} | 1 2,3 | All | | ±1.0 ±10 | μA |
| Digital Input Leakage Current | I _{IN} | V _{DD} =+15V V _{IN} =0V or V _{DD} | 1 2,3 | All | | ±1.0 ±10 | μA |
| Supply Current | I _{DD} | V _{DD} =+5V All digital inputs V _{DD} =+15V V _{IL} or V _{IH} | 1,2,3 | All | | 2.0 2.0 | mA |
| Supply Current | I _{DD} | V _{DD} =+5V & +15V. All digital inputs 0V or V _{DD} | 1 2,3 | All | | 100 500 | μA |
| Gain Temperature Coefficient NOTE 3 | TC _{AE} | V _{DD} =+5V V _{DD} =+15V | 1,2,3 | All | | ±70 ±35 | ppm/°C |
| Feedthrough Error V _{REFA} to OUTA and V _{REFB} to OUTB | FT _{REFA} | V _{DD} =+5V or V _{DD} =+15V, V _{REF} =+10V, 100kHz sinewave, DAC latches loaded with 0000 0000 NOTE 3, NOTE 5 | 4,5,6 | All | | -55 | dB |

| TEST | Symbol | CONDITIONS | | Group A Subgroup | Device type | Limits Min | Limits Max | Units |
|---|--|---|--|------------------|-------------|------------|------------|-------|
| | | -55 °C ≤ T _A ≤ +125 °C 1/ Unless otherwise specified | | | | | | |
| Digital Input Capacitance NOTE 3, 6 | C _{IN} | V _{DD} =+5V and V _{DD} =+15V, DB0-DB7 | | 4 | All | | 10 | pF |
| Digital Input Capacitance NOTE 3, 6 | C _{IN} | V _{DD} =+5V _____ & WR, CS, DACA/DACB V _{DD} =+15V | | 4 | All | | 15 | pF |
| ANALOG INPUTS | | | | | | | | |
| Digital Output pin 2 Capacitance 3/ pin 20 | C _{OUTA} C _{OUTB} | V _{DD} =+5V and 15V, DAC latches loaded with 0000 0000 | | 4 | All | | 50 50 | pF |
| Digital Output pin 2 Capacitance 3/ pin 20 | C _{OUTA} C _{OUTB} | V _{DD} =+5V and 15V, DAC latches loaded with 1111 1111 | | 4 | All | | 120 120 | pF |
| TIMING | | | | | | | | |
| Chip select to write setup time NOTE 3, 7 | t _{CS} | V _{DD} =+5V V _{DD} =+15V | | 9,10,11 | All | 250 180 | | ns |
| Chip select to write hold time NOTE 3, 7 | t _{CH} | V _{DD} =+5V V _{DD} =+15V | | 9,10,11 | All | 20 10 | | ns |
| Write pulse width NOTE 3, 7 | t _{WR} | V _{DD} =+5V, t _{CS} ≥ t _{WR} , t _{CH} ≥ 0 V _{DD} =+15V, t _{CS} ≥ t _{WR} , t _{CH} ≥ 0 | | 9,10,11 | All | 220 180 | | ns |
| Data valid to write setup time NOTE 3, 7 | t _{DS} | V _{DD} =+5V V _{DD} =+15V | | 9,10,11 | All | 220 180 | | ns |
| Data valid to write hold time NOTE 3, 7 | t _{DH} | V _{DD} =+5V V _{DD} =+15V | | 9,10,11 | All | 10 10 | | ns |
| Data select to write setup time NOTE 3,7 | t _{AS} | V _{DD} =+5V V _{DD} =+15V | | 9,10,11 | All | 250 180 | | ns |
| Data select to write hold time NOTE 7 | t _{AH} | V _{DD} =+5V V _{DD} =+15V | | 9,10,11 | All | 20 10 | | ns |
| Reference input resistance match | R _{MIN} ΔV _{REF} | V _{DD} =+5V V _{DD} =+15V | | 4,5,6 | All | | ±1 ±1 | % |
| Channel to Channel isolation NOTE 3 V _{REFA} to OUTB | CHISO | V _{DD} =+5V or +15V. V _{REFA} =±10V, 100kHz sinewave, V _{REFB} =0V | | 4,5,6 | All | | -60 | dB |
| Channel to Channel isolation NOTE 3 V _{REFB} to OUTA | CHISO | V _{DD} =+5V or +15V. V _{REFB} =±10V, 100kHz sinewave, DAC, V _{REFA} =0V | | 4,5,6 | All | | -60 | dB |
| Output Current Settling Time NOTE 3, NOTE 8 | t _{SL} | V _{DD} =+5V V _{DD} =+15V | | 9,10,11 | All | | 600 350 | ns |

NOTE 1: V_{OUT1}=0V; V_{REF}=+10V, AGND=DGND unless otherwise specified.

NOTE 2: Measured using internal RFBA and RFBB. Gain error is adjustable.

NOTE 3: Characteristics supplied for use as a typical design limit, but not production tested.

- NOTE 4: Guaranteed, if not tested.
 NOTE 5: Feedthrough error can be reduced by connecting the metal lid to ground.
 NOTE 6: Subgroup 4 (C_{IN} and C_{OUT} measurements) shall be measured only for the initial test and after process or design changes which may affect capacitance.
 NOTE 7: Timing in accordance with Write Cycle Timing Diagram in Commercial Data Sheet.
 NOTE 8: To 0.5LSB, $OUTA/OUTB=100\Omega$ in parallel with 13pF. \overline{CS} \overline{WR}
 $DB0-DB7=0V$ to V_{DD} or V_{DD} to $0V$, $WR=CS=0V$

MODE SELECTION TABLE:

| \overline{CS} | \overline{WR} | $\overline{DACA/DACB}$ | DACA | DACB |
|-----------------|-----------------|------------------------|-------|-------|
| L | L | L | Write | Hold |
| L | L | H | Hold | Write |
| H | X | X | Hold | Hold |
| X | H | X | Hold | Hold |

L = Low state, H = High state, X = Don't care

ORDERING INFORMATION:

| | Package | Pkg. Code | |
|----|---------------|-----------|---------------|
| 01 | 20 pin CERDIP | J20 | MX7528SQ/883B |
| 02 | 20 pin CERDIP | J20 | MX7528TQ/883B |
| 03 | 20 pin CERDIP | J20 | MX7528UQ/883B |

TERMINAL CONNECTIONS:

| Pin | J20 |
|-----|------------------------|
| 1 | AGND |
| 2 | OUTA |
| 3 | RFBA |
| 4 | VREFA |
| 5 | DGND |
| 6 | $\overline{DACA/DACB}$ |
| 7 | (MSB)DB7 |
| 8 | DB6 |
| 9 | DB5 |
| 10 | DB4 |
| 11 | DB3 |
| 12 | DB2 |
| 13 | DB1 |
| 14 | DB0(LSB) |
| 15 | \overline{CS} |
| 16 | \overline{WR} |
| 17 | V_{DD} |
| 18 | VREFB |
| 19 | RFBB |
| 20 | OUTB |

QUALITY ASSURANCE

Sampling and inspection procedures shall be in accordance with MIL-Prf-38535, Appendix A as specified in Mil-Std-883.

Screening shall be in accordance with Method 5004 of Mil-Std-883. Burn-in test Method 1015:

1. Test Condition, A, B, C, or D.
2. TA = +125°C minimum.
3. Interim and final electrical test requirements shall be specified in Table 2.

Quality conformance inspection shall be in accordance with Method 5005 of Mil-Std-883, including Groups A, B, C, and D inspection.

Group A inspection:

1. Tests as specified in Table 2.
2. Selected subgroups in Table 1, Method 5005 of Mil-Std-883 shall be omitted.

Group C and D inspections:

- a. End-point electrical parameters shall be specified in Table 1.
- b. Steady-state life test, Method 1005 of Mil-Std-883:
 1. Test condition A, B, C, D.
 2. TA = +125°C, minimum.
 3. Test duration, 1000 hours, except as permitted by Method 1005 of Mil-Std-883.

TABLE 2. ELECTRICAL TEST REQUIREMENTS

| Mil-Std-883 Test Requirements | Subgroups per Method 5005, Table 1 |
|--|------------------------------------|
| Interim Electric Parameters Method 5004 | 1 |
| Final Electrical Parameters Method 5005 | 1*, 2, 3 |
| Group A Test Requirements Method 5005 | 1, 2, 3, 4, 5, 6, 9**, 10**, 11** |
| Group C and D End-Point Electrical Parameters Method 5005 | 1 |

* PDA applies to Subgroup 1 only.

** Subgroups 9, 10 and 11, if not tested shall be guaranteed to the limits specified in Table 1.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.